

FEATURES

| $V_{DS}=60V, R_{DS(ON)} \leq 1.7\Omega @ V_{GS}=10V, I_D=1A$

| Low gate charge and ESD protected

| For load switching, low current inverters and low current DC-DC converters applications

APPLICATION

| Case: SOT-23

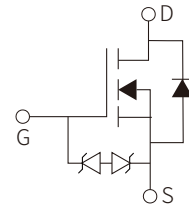
| Case Material: Molded Plastic. UL flammability

| Classification Rating: 94V-0

APPROVALS

RoHS Compliance with 2011/65/EU

HF Compliance with IEC61249-2-21:2003



ABSOLUTE MAXIMUM RATINGS($T_A=25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	60	V
Drain Current-Continuous	$T_A=25^\circ\text{C}$	I_D	0.65	A
Drain Current-Continuous	$T_A=70^\circ\text{C}$	I_D	0.5	A
Pulsed Drain Current		I_{DM}	1.6	A
Gate-Source Voltage		V_{GS}	± 20	V
Total Power Dissipation	$T_A=25^\circ\text{C}$	P_D	1.4	W
Total Power Dissipation	$T_A=70^\circ\text{C}$	P_D	0.9	W
Thermal resistance from Junction to ambient		$R_{\theta JA}$	125	$^\circ\text{C/W}$
Junction temperature		T_J	150	$^\circ\text{C}$
Storage temperature		T_{STG}	-55 to 150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-source Breakdown Voltage*	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current*	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1	μA
Gate-Body Leakage*	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 10	μA
Gate Threshold Voltage*	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	2.2	2.5	V
Static Drain-Source On-Resistance*	$R_{DS(on)}$	$V_{GS}=10V, I_D=0.65A$		1.4	1.7	Ω
		$V_{GS}=10V, I_D=0.65A, T_J=125^{\circ}\text{C}$		2.5	3	
		$V_{GS}=4.5V, I_D=0.5A$		1.6	2	
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=0.65A$		0.8		S
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V, f=1.0\text{MHz}$		22	27	pF
Output Capacitance	C_{oss}			6	10	
Reverse Transfer Capacitance	C_{rss}			2	6	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V, R_L=75\Omega$ $V_{DS}=30V, R_{GEN}=3\Omega$		5.3	12	ns
Turn-On Rise Time	t_r			2.8	6	
Turn-Off Delay Time	$t_{d(off)}$			19.7	30	
Turn-Off Fall Time	t_f			5.5	11	
Diode forward voltage	V_{SD}	$I_S=1A, V_{GS}=0V$		0.8	1	V
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=30V, I_D=0.65A$		0.8	2	nC
Gate Source Charge	Q_{gs}			0.17	1	
Gate Drain Charge	Q_{gd}			0.2	1	
Diode forward current	I_S				1.2	A
Body Diode Reverse Recovery Time	t_{rr}	$I_F=0.65A, di/dt=100A/\mu s, V_{GS}=9V$		11.3	14	ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=0.65A, di/dt=100A/\mu s, V_{GS}=9V$		7.5		nC

*Pulse test ; Pulse width $\leq 300\mu s$, Duty cycle $\leq 0.5\%$

PARAMETER CHARACTERISTIC CURVE

Fig 1: On-Region Characteristics

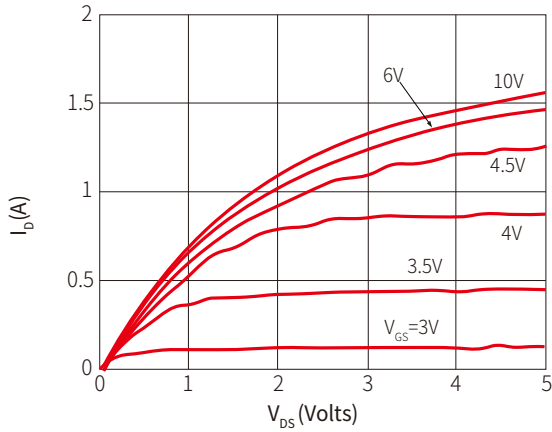


Figure 2: Transfer Characteristics

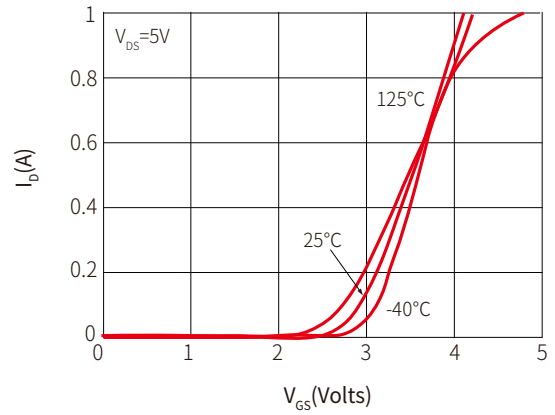


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

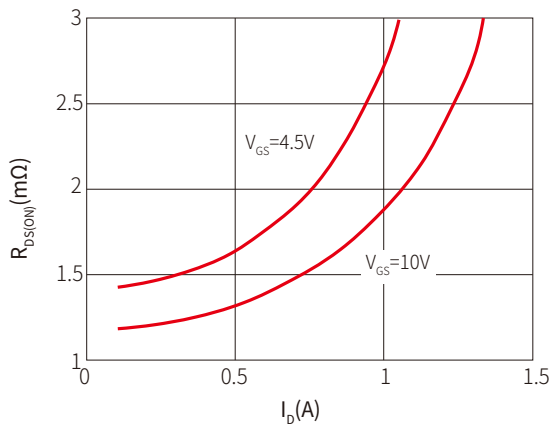


Figure 4: On-Resistance vs. Junction Temperature

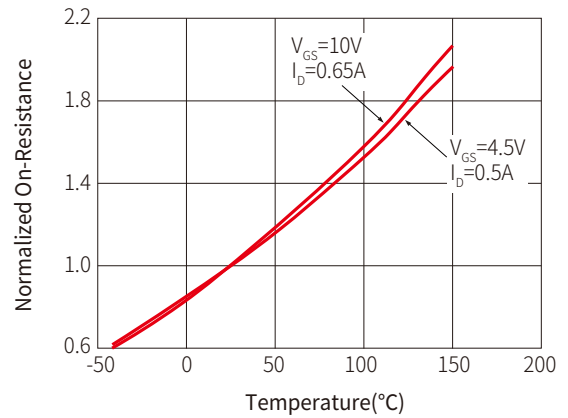


Figure 5: On-Resistance vs. Gate-Source Voltage

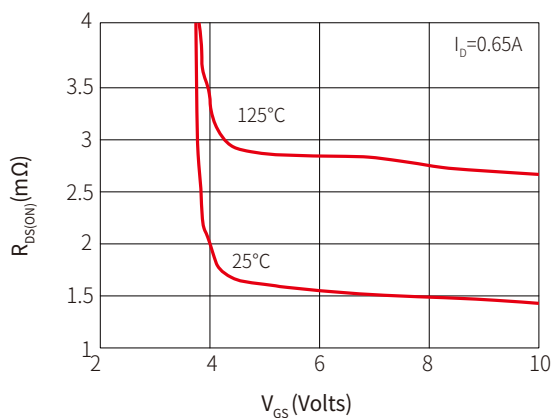


Figure 6: Body-Diode Characteristics

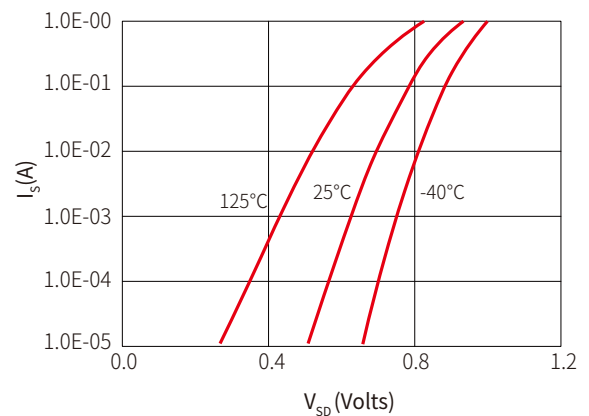
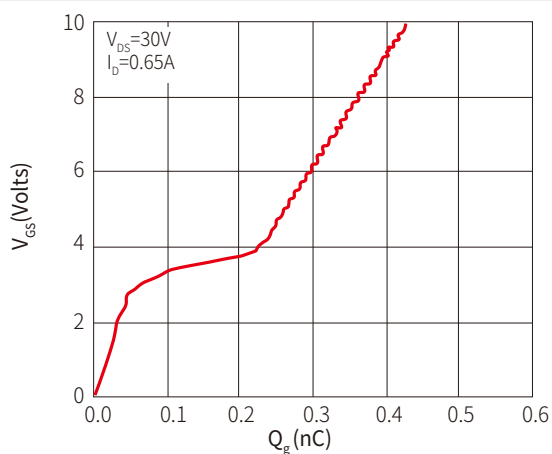
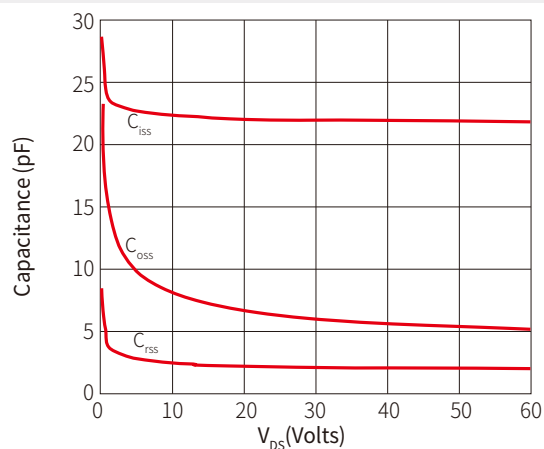
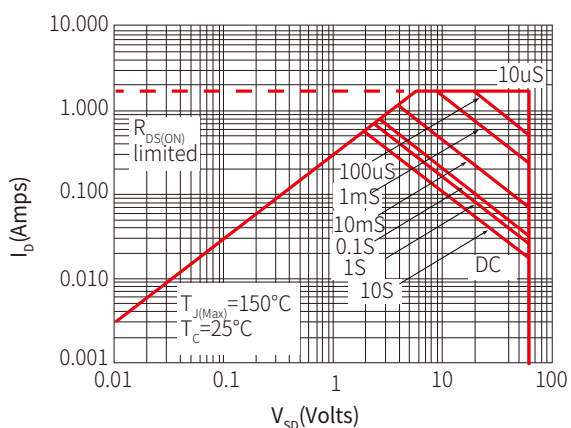
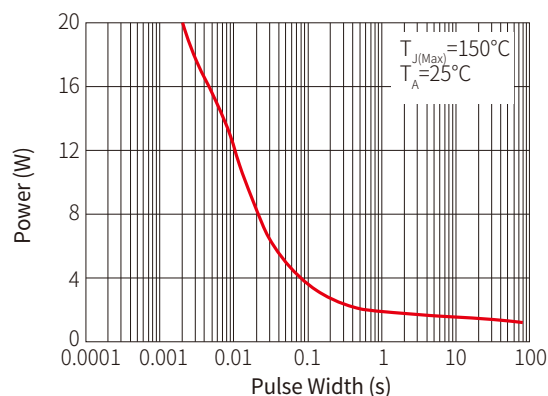
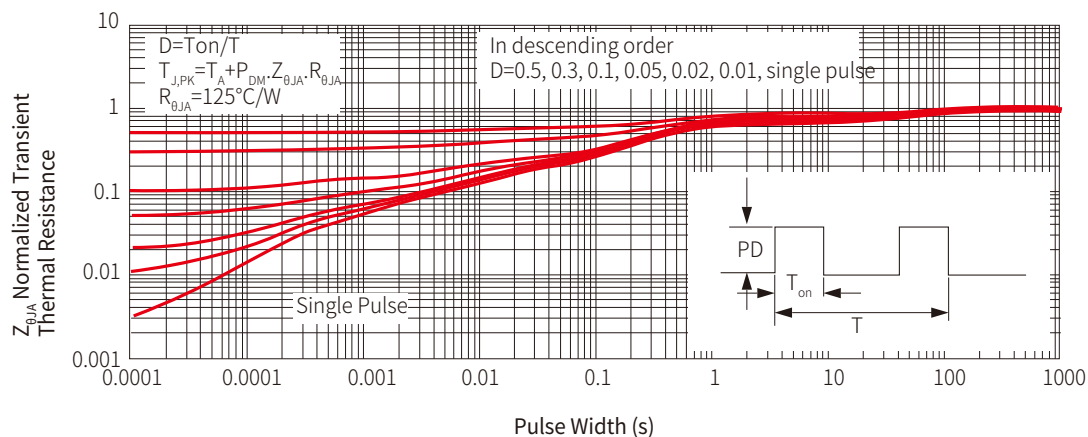
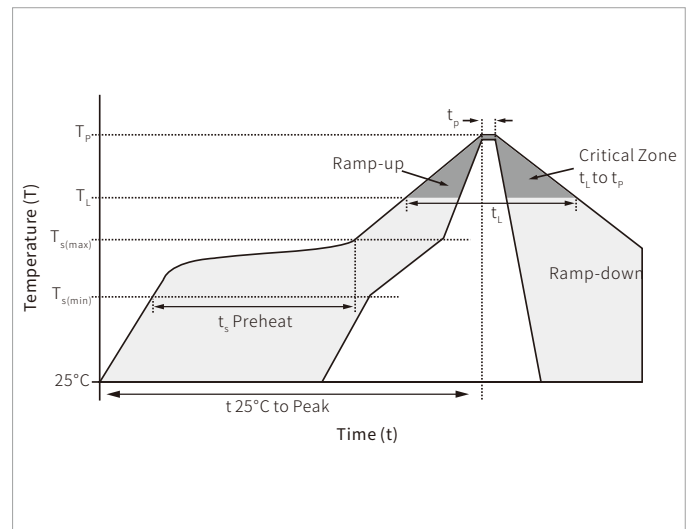


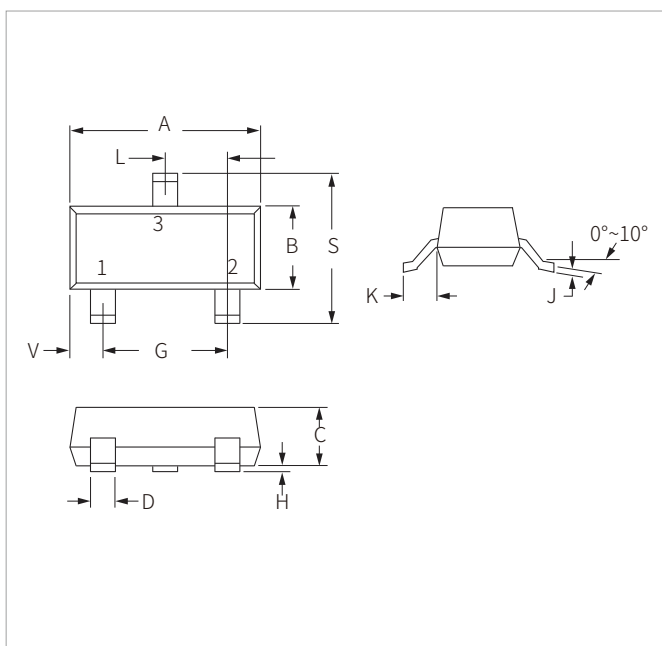
Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Characteristics

Figure 9: Maximum Forward Biased Safe Operating Are

Figure 10: Single Pulse Power Rating Junction-to-Ambient

Figure 11: Normalized Maximum Transient Thermal Impedance


SOLDERING PARAMETERS

Reflow Condition		Lead-free assembly
Pre Heat	Temperature Max ($T_{s(min)}$)	150°C
	Temperature Max ($T_{s(max)}$)	200°C
	Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp (T_L) to peak		3°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/second max
Reflow	Temperature (T_L) (Liquidus)	217°C
	Time (min to max) (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260°C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes max.
Do not exceed		260°C

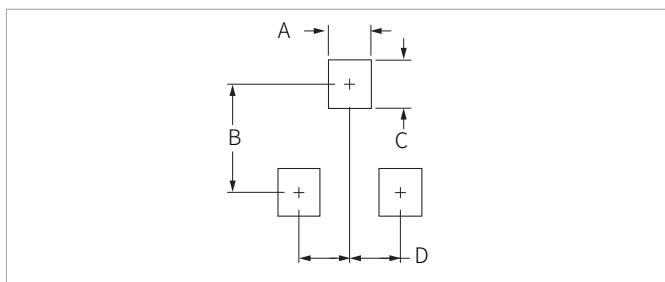


SOT-23 PACKAGE INFORMATION



Ref.	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.80	3.05	0.110	0.120
B	1.20	1.40	0.047	0.055
C	0.90	1.15	0.035	0.045
D	0.37	0.50	0.015	0.020
G	1.75	2.05	0.069	0.081
H	0.01	0.100	0.001	0.004
J	0.085	0.180	0.003	0.007
K	0.35	0.69	0.014	0.029
L	0.89	1.02	0.035	0.040
S	2.10	2.65	0.083	0.104
V	0.45	0.60	0.018	0.024

RECOMMENDED PAD LAYOUT DIMENSIONS



Ref.	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.71	0.97	0.028	0.038
B	1.88	2.13	0.074	0.084
C	0.71	0.97	0.028	0.038
D	0.81	1.07	0.032	0.042

ORDERING INFORMATION

Part Number	Component Package	QTY/Reel	Reel Size
SNM3460S	SOT-23	3000PCS	7"

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